

### General Description

The WSD3055GDN56 is the highest performance SGT Dual N-Channel MOSFET with extreme high cell density, which provide excellent  $R_{DS(ON)}$  and gate charge for most of the synchronous buck converter applications.

The WSD3055GDN56 meet the RoHS and Green Product requirement, 100%  $E_{AS}$  guaranteed with full function reliability approved.

### Features

- 100% UIS Tested.
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

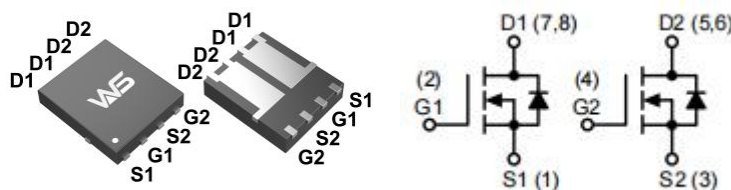
### Product Summary

$BV_{DSS}$	$R_{DS(ON)}$	$I_D$
30V	5.5mΩ	45A

### Applications

- Power Management for Industrial DC/DC Converters
- Ideal for high-frequency switching and synchronous rectification

### DFN5\*6-8L Pin Configuration



### Absolute Maximum Ratings ( $T_A=25^{\circ}\text{C}$ , Unless Otherwise Noted)

Symbol	Parameter		Rating	Units
$V_{DS}$	Drain-Source Voltage		30	V
$V_{GS}$	Gate-Source Voltage		$\pm 20$	
$I_D$ <sup>7</sup>	Continuous Drain Current	$T_C=25^{\circ}\text{C}$	45	A
		$T_C=100^{\circ}\text{C}$	30	
$I_{DM}$ <sup>3</sup>	Pulse Drain Current		90	
$P_D$ <sup>2</sup>	Power Dissipation	$T_C=25^{\circ}\text{C}$	27	W
$I_{AS}$ <sup>3</sup>	Single pulse Avalanche Current		60	A
$E_{AS}$ <sup>3</sup>	Single pulse Avalanche Energy	$L=0.5\text{mH}$	90	mJ
$T_{STG}$	Storage Temperature Range		-55 to 150	$^{\circ}\text{C}$
$T_J$	Operating Junction Temperature Range		-55 to 150	
$R_{\theta JA}$ <sup>1,4</sup>	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	30	$^{\circ}\text{C/W}$
		Steady State	60.5	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		3.1	

**Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , Unless Otherwise Noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=250\mu A$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$ , $I_D=20A$	---	5.5	6.3	m $\Omega$
		$T_J=125^{\circ}\text{C}$	---	11	---	
		$V_{GS}=4.5V$ , $I_D=15A$	---	6.0	7.4	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=250\mu A$	1.0	1.4	2.0	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=30V$ , $V_{GS}=0V$	---	---	1.0	$\mu A$
		$T_J=55^{\circ}\text{C}$	---	---	5.0	
$I_{GSS}$	Gate-Source Leakage Current	$V_{DS}=0V$ , $V_{GS}=\pm 10V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V$ , $I_D=20A$	---	30	---	S
$R_G$	Gate Resistance	$f=1.0\text{MHz}$	1.0	2.0	3.0	$\Omega$
$Q_g$	Total Gate Charge (10V)	$V_{DS}=15V$ , $V_{GS}=10V$ , $I_D=20A$	---	15	---	nC
$Q_{gs}$	Gate-Source Charge		---	2.9	---	
$Q_{gd}$	Gate-Drain Charge		---	2.1	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=5V$ , $V_{GS}=10V$ , $I_D=20A$ $R_L=1\Omega$ , $R_{GEN}=3\Omega$	---	6.5	---	ns
$T_r$	Rise Time		---	2.5	---	
$T_{d(off)}$	Turn-Off Delay Time		---	17	---	
$T_f$	Fall Time		---	2.3	---	
$C_{iss}$	Input Capacitance	$V_{DS}=15V$ , $V_{GS}=0V$ , $f=1.0\text{MHz}$	---	780	---	pF
$C_{oss}$	Output Capacitance		---	220	---	
$C_{rss}$	Reverse Transfer Capacitance		---	15.3	---	

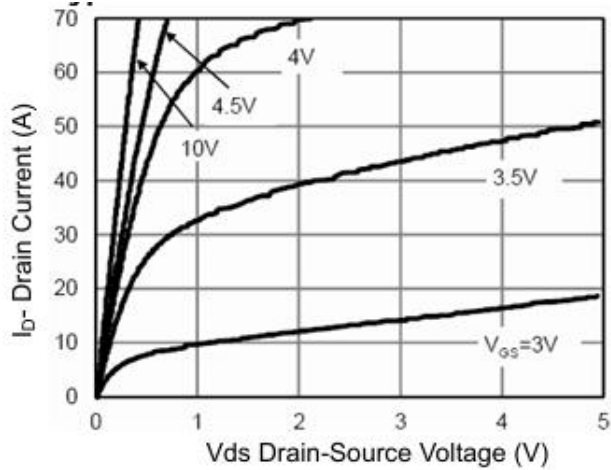
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$I_S$ <sup>7</sup>	Continuous Source Current		---	---	45	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V$ , $I_S=1A$	---	0.7	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=20A$ , $di/dt=500A/\mu s$	---	10	---	ns
$Q_{rr}$	Reverse Recovery Charge		---	19	---	nC

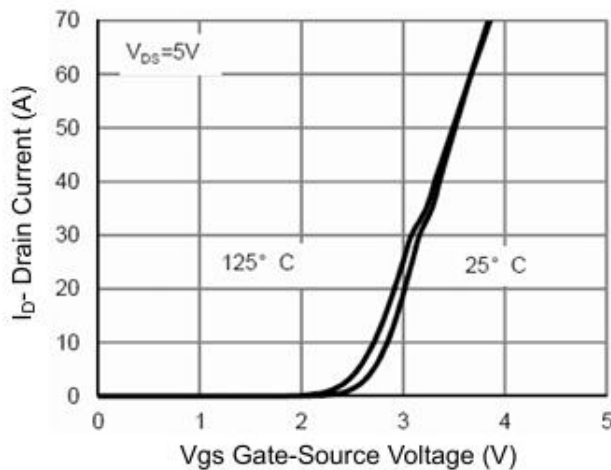
**Note:**

- The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The Power dissipation  $P_{DSM}$  is based on  $R_{\theta JA} \leq 10s$  and the maximum allowed junction temperature of  $150^{\circ}\text{C}$ . The value in any given application depends on the user's specific board design.
- The power dissipation  $P_D$  is based on  $T_{J(MAX)}=150^{\circ}\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- Single pulse width limited by junction temperature  $T_{J(MAX)}=150^{\circ}\text{C}$ .
- The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to case  $R_{\theta JC}$  and case to ambient.
- The static characteristics in Figures 1 to 6 are obtained using  $<300\mu s$  pulses, duty cycle 0.5% max.
- These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of  $T_{J(MAX)}=150^{\circ}\text{C}$ . The SOA curve provides a single pulse rating.
- The maximum current rating is package limited.
- These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ .
- The maximum current rating is silicon limited

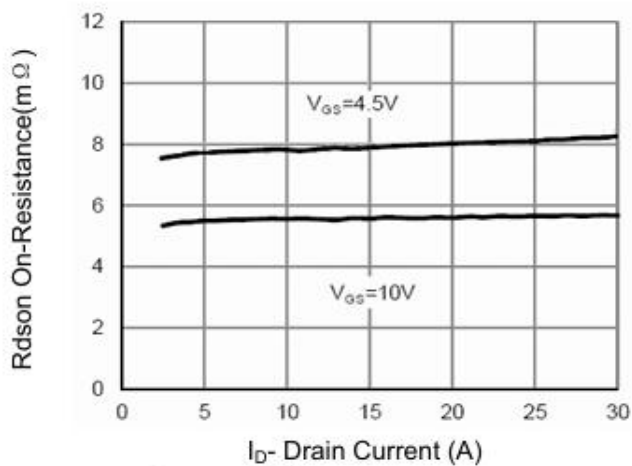
## Typical Characteristics



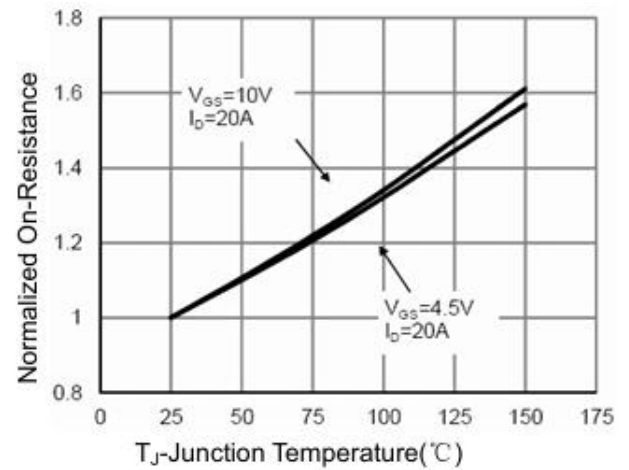
**Figure 1 Output Characteristics**



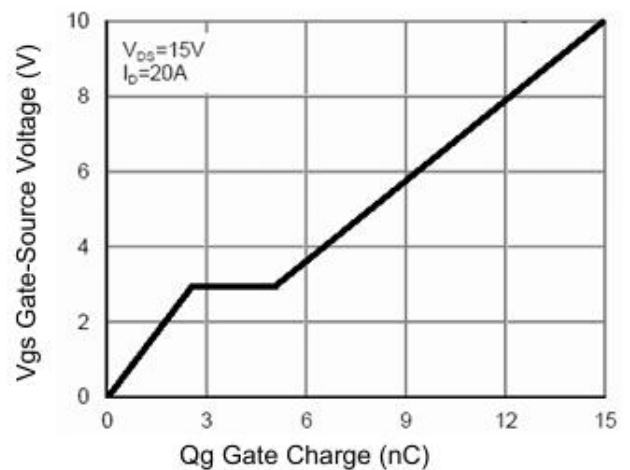
**Figure 2 Transfer Characteristics**



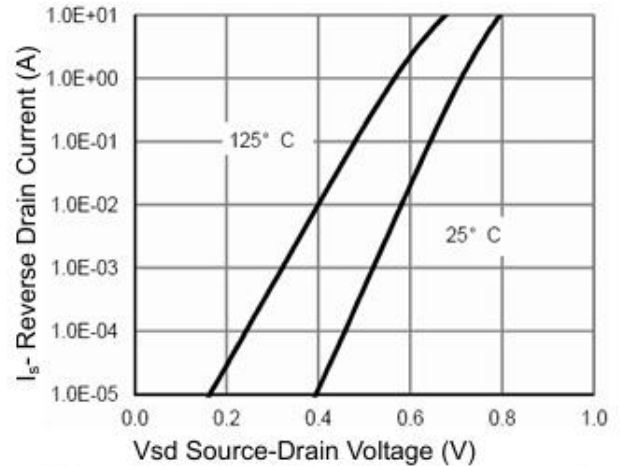
**Figure 3 Rdson- Drain Current**



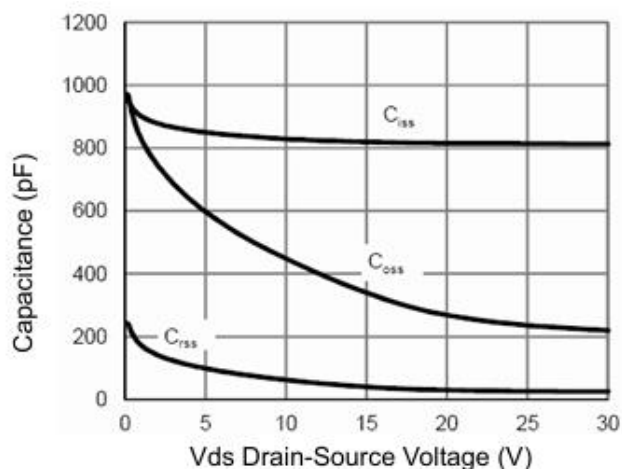
**Figure 4 Rdson-Junction Temperature**



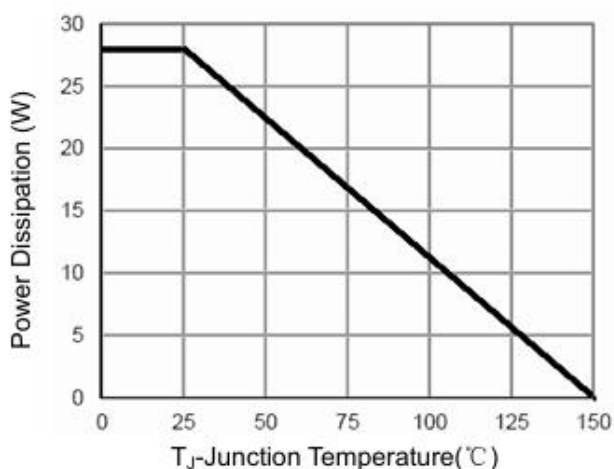
**Figure 5 Gate Charge**



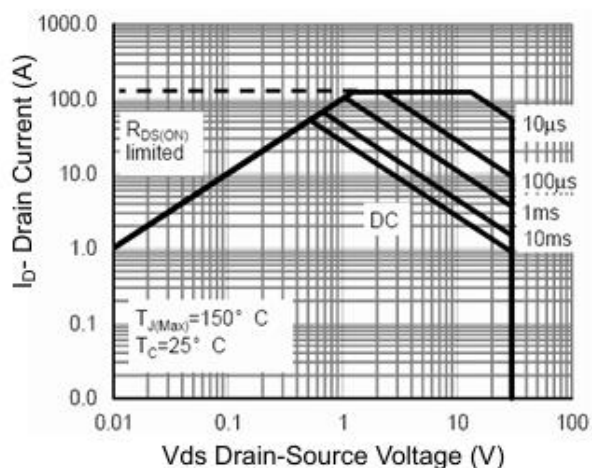
**Figure 6 Source- Drain Diode Forward**



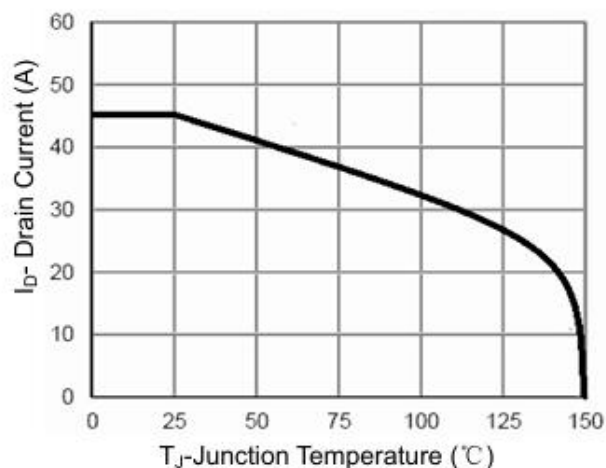
**Figure 7 Capacitance vs Vds**



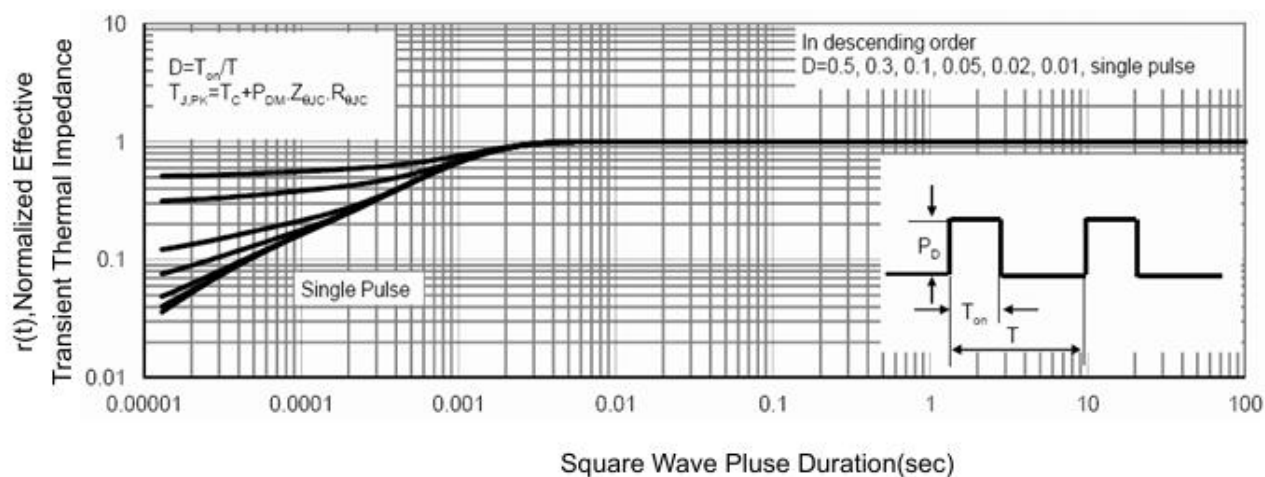
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**

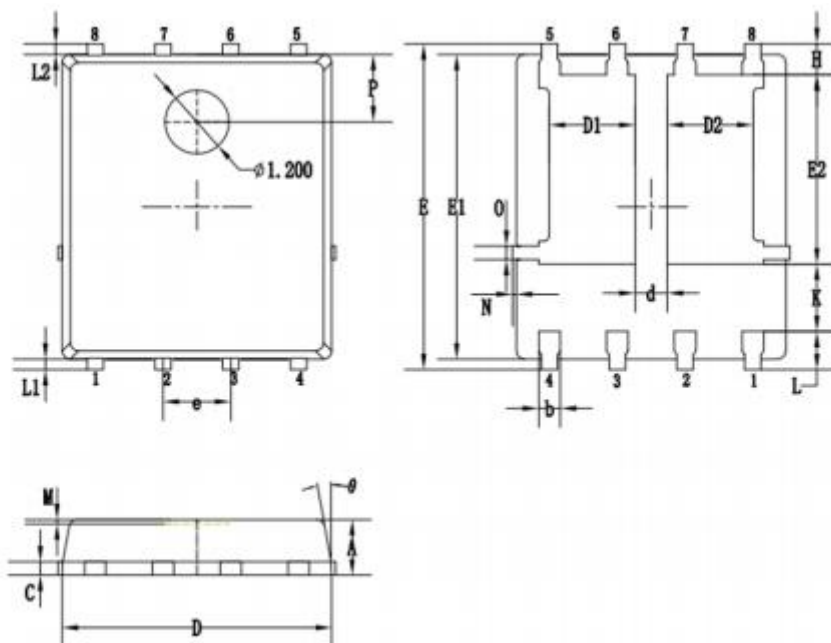


**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## Packaging information



SYMBOLS	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1/D2	1.51	1.61	1.71
d	0.50	0.60	0.70
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
$\theta$	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		



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